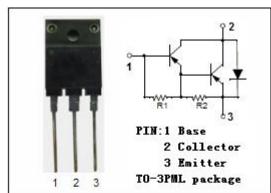


isc Silicon PNP Darlington Power Transistor

2SB1382

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
- : V_{(BR)CEO}= -120V(Min)
- · High DC Current Gain-
 - : h_{FE} = 2000(Min.) @(I_{C} = -8A, V_{CE} = -4V)
- · Low Collector Saturation Voltage-
 - : $V_{CE(sat)} = -1.5V(Max)@ (I_C = -8A, I_B = -16mA)$
- Complement to Type 2SD2082
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

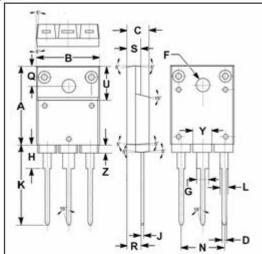


APPLICATIONS

 Designed for chopper regulator, DC motor driver and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	-120	V
V _{CEO}	Collector-Emitter Voltage	-120	V
V _{EBO}	Emitter-Base Voltage	-6	V
lc	Collector Current-Continuous	-16	Α
Ісм	Collector Current-Peak	-26	А
lв	Base Current-Continuous	ase Current-Continuous -1	
Pc	Collector Power Dissipation @Tc=25℃	75	W
TJ	Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature	-55~150	$^{\circ}$



	mm	
DIM	MIN	MAX
Α	19.90	20.10
В	15.75	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
Н	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
0	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10



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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

1)-25 C uniess otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA ; I _B = 0	-120			V			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -8A; I _B = -16mA			-1.5	V			
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -8A; I _B = -16mA			-2.5	V			
Ісво	Collector Cutoff Current	V _{CB} = -120V ; I _E = 0			-10	μА			
I _{EBO}	Emitter Cutoff Current	V _{EB} = -6V; I _C = 0			-10	mA			
h _{FE}	DC Current Gain	I _C = -8A ; V _{CE} = -4V	2000						
Сов	Output Capacitance	I _E = 0; V _{CB} = -10V; f _{test} = 1MHz		350		pF			
f _T	Current-Gain—Bandwidth Product	I _E = 1A ; V _{CE} = -12V		50		MHz			
Switching Times									
ton	Turn-on Time			0.8		μS			
t _{stg}	Storage Time	$V_{CC}^{=}$ -40V, R_L = 5 Ω , I_C = -8A; I_{B1} = - I_{B2} = -16mA,		1.8		μS			
t _f	Fall Time			1.0		μS			



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